Dual Low Noise Amplifier Packaged Chip

AASL818AQ

Product Specification

V1.0

1. Product Features

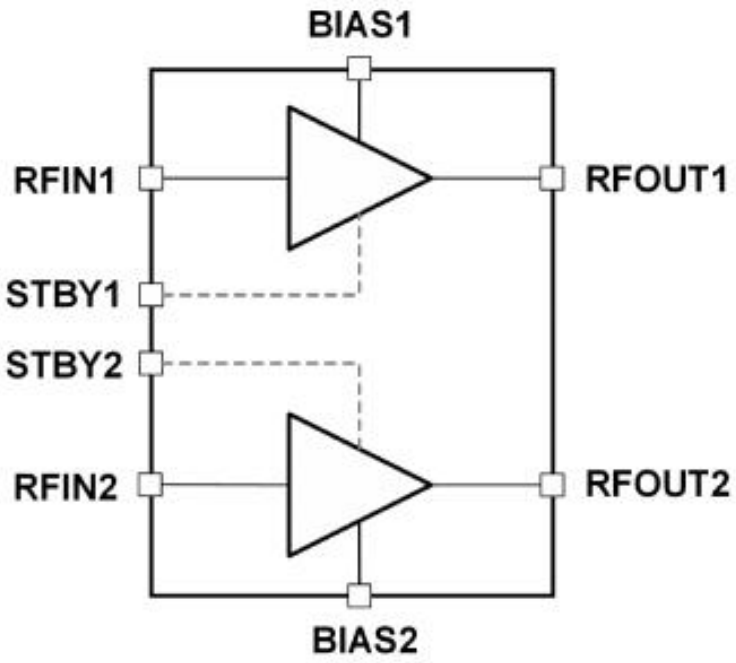
- Frequency Range: 1.5 ~ 2.3 GHz
- Small-signal Gain: 22.5 dB
- Output P1dB: 25 dBm
- Noise Figure: 0.6 dB
- OIP3: 37.5 dBm
- Bias Condition: VDD = 5 V, IDD = 110 mA, Zin/Zout = 50 Ω
- Chip Dimensions: 4 mm × 4 mm × 0.75 mm

2. Functional Description

This chip is a dual low noise amplifier packaged chip operating at 1.5 ~ 2.3 GHz. It operates from a single 5 V supply. At a supply current of 110 mA, it provides a gain of 22.5 dB, an output P1dB of 25 dBm, an output third-order intercept point (OIP3) of 37.5 dBm, and a noise figure of 0.6 dB.

This chip is suitable for applications such as communications and radar.

3. Block Diagram



4. Typical Applications

- 3G, 4G, 5G wireless infrastructure
- Public security infrastructure
- General-purpose RF applications

5. Electrical Performance Parameters

5.1 RF Characteristics

Unless otherwise specified, all electrical characteristics are measured under small-signal conditions at TA = +25 ° C, in a 50 Ω continuous wave system.